

### NCE N-Channel Enhancement Mode Power MOSFET

#### **Description**

The NCE6003X uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge. This device is suitable for use as a Battery protection or in other switching application.

#### **General Features**

V<sub>DS</sub> =60V,I<sub>D</sub> =3A

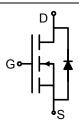
 $R_{DS(ON)}$  <90m $\Omega$  @  $V_{GS}$ =10V

 $R_{DS(ON)} < 110 m\Omega$  @  $V_{GS} = 4.5 V$ 

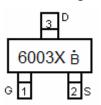
- High power and current handing capability
- Lead free product is acquired
- Surface mount package

### **Application**

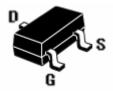
- Battery switch
- ●DC/DC converter



#### **Schematic Diagram**



**Marking and Pin Assignment** 



**SOT-23 Top View** 

#### **Package Marking and Ordering Information**

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
6003X	NCE6003X	SOT-23	Ø180mm	8 mm	3000 units

#### Absolute Maximum Ratings (T<sub>A</sub>=25℃unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V <sub>DS</sub>	60	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Drain Current-Continuous	I <sub>D</sub>	3	Α
Drain Current-Pulsed (Note 1)	I <sub>DM</sub>	10	Α
Maximum Power Dissipation	P <sub>D</sub>	1.7	W
Operating Junction and Storage Temperature Range	$T_{J},T_{STG}$	-55 To 150	$^{\circ}$

#### **Thermal Characteristic**

Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{ heta JA}$	73.5	°C/W
, and the second	****		

#### Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V I <sub>D</sub> =250μA	60	-	-	٧
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =60V,V <sub>GS</sub> =0V	-	-	1	μΑ



# http://www.ncepower.com

# **NCE6003X**

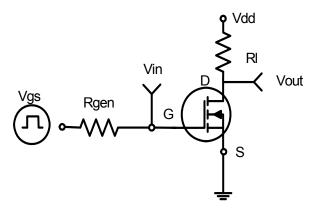
Gate-Body Leakage Current	I <sub>GSS</sub>	$V_{GS}=\pm20V, V_{DS}=0V$	-	-	±100	nA
On Characteristics (Note 3)	·					
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250μA	0.9	1.3	2.0	V
Drain-Source On-State Resistance	D	$V_{GS}$ =10V, $I_D$ =3A	-	68	90	mΩ
Dialii-Source Oil-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =4.5V, I <sub>D</sub> =3A	-	80	110	mΩ
Forward Transconductance	<b>g</b> FS	$V_{DS}$ =5 $V$ , $I_{D}$ =3 $A$	-	3	-	S
Dynamic Characteristics (Note4)	·					
Input Capacitance	C <sub>lss</sub>	\/ -20\/\/ -0\/	-	270	-	PF
Output Capacitance	Coss	$V_{DS}$ =30V, $V_{GS}$ =0V, F=1.0MHz	-	16	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>	F=1.0WHZ	-	15	-	PF
Switching Characteristics (Note 4)	·					
Turn-on Delay Time	t <sub>d(on)</sub>		-	5	-	nS
Turn-on Rise Time	t <sub>r</sub>	$V_{DD}$ =30V, $I_{D}$ =3A $V_{GS}$ =10V, $R_{GEN}$ =1 $\Omega$	-	10	-	nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	12	-	nS
Turn-Off Fall Time	t <sub>f</sub>		-	8	-	nS
Total Gate Charge	$Q_g$	$V_{DS}$ =30V, $I_{D}$ =3A, $V_{GS}$ =10V	-	10.2	-	nC
Gate-Source Charge	$Q_{gs}$		-	1.8	-	nC
Gate-Drain Charge	$Q_{gd}$	VGS-10V	-	2.2	-	nC
Drain-Source Diode Characteristics	·					
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V,I <sub>S</sub> =3A	-	-	1.2	V
Diode Forward Current (Note 2)	Is		-	-	3	Α

#### Notes:

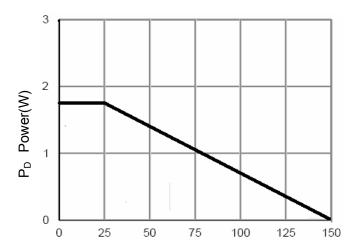
- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- Surface Mounted on FR4 Board, t ≤ 10 sec.
   Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 4. Guaranteed by design, not subject to production



## **Typical Electrical and Thermal Characteristics**



**Figure 1:Switching Test Circuit** 



 $T_J$ -Junction Temperature( ${}^{\circ}$ C)

Figure 3 Power Dissipation

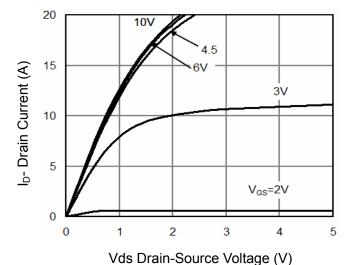


Figure 5 Output Characteristics

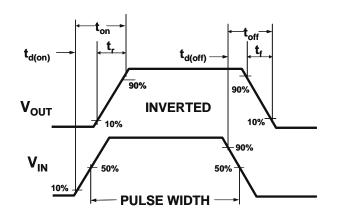
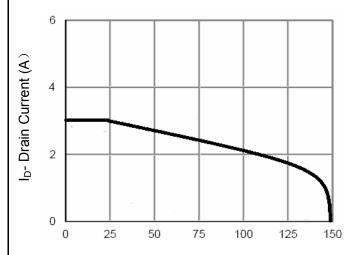


Figure 2:Switching Waveforms



T<sub>J</sub>-Junction Temperature(°C)

Figure 4 Drain Current

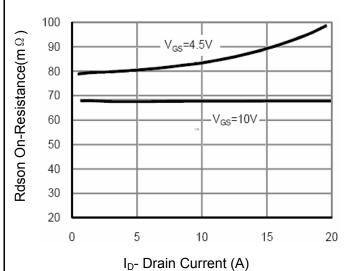
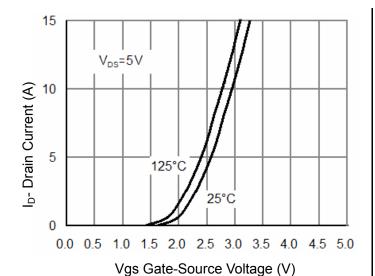
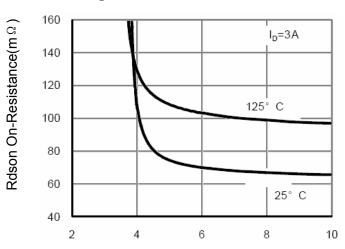


Figure 6 Drain-Source On-Resistance





**Figure 7 Transfer Characteristics** 



Vgs Gate-Source Voltage (V)

Figure 9 Rdson vs Vgs

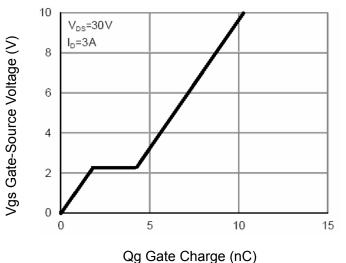


Figure 11 Gate Charge

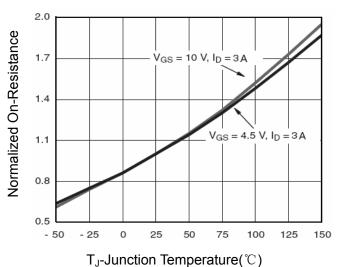


Figure 8 Drain-Source On-Resistance

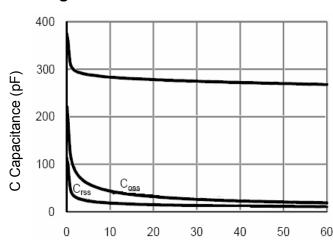


Figure 10 Capacitance vs Vds

Vds Drain-Source Voltage (V)

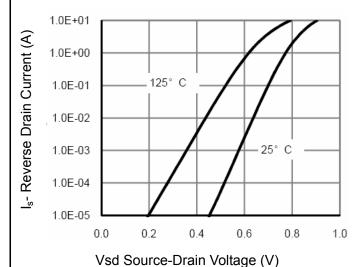
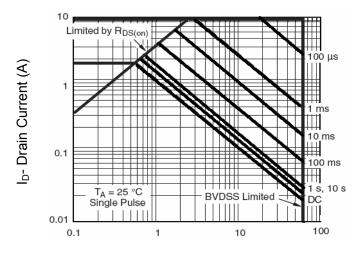


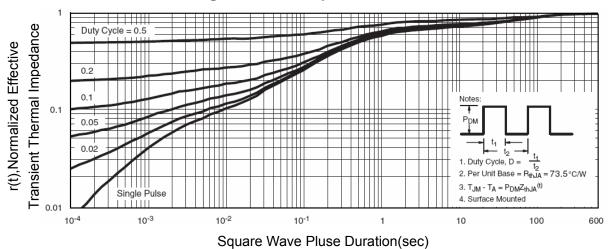
Figure 12 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

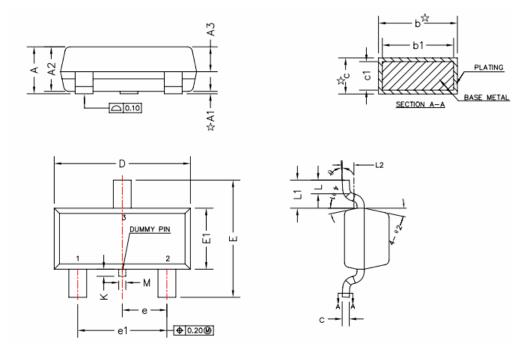
Figure 13 Safe Operation Area



**Figure 14 Normalized Maximum Transient Thermal Impedance** 



# **SOT-23 Package Information**



Symbol	Millimeters			
Syllibol	Min.	Max.		
Α	0.89	1.12		
A1	0.01	0.10		
A2	0.88	1.02		
A3	0.43	0.63		
b	0.36	0.50		
b1	0.35	0.45		
С	0.14	0.20		
c1	0.14	0.16		
D	2.80	3.00		
E	2.35	2.64		
E1	1.20	1.40		
е	0.90	1.00		
e1	1.80	2.00		
L	0.40	0.60		
L1	0.6REF			
L2	0.25BSC			
M	0.10	0.25		
K	0.00	0.25		
θ	0°	8°		
θ1	10°	14°		
θ2	10°	14°		



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